



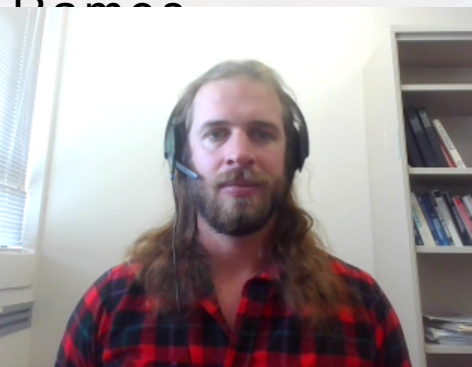
Losses in superconducting circuits fabricated on thin silicon membranes for hybrid quantum systems integration

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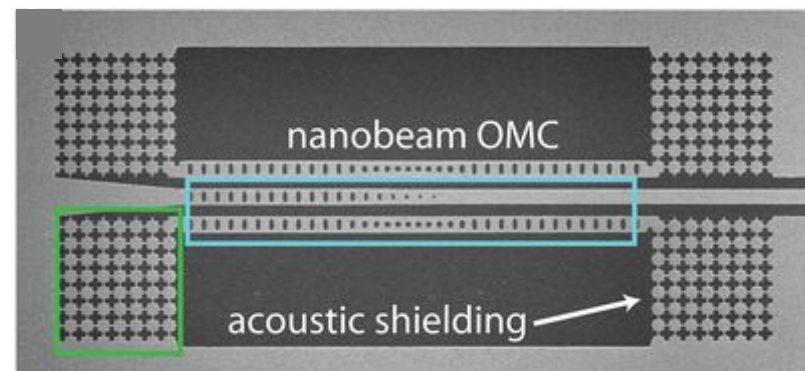
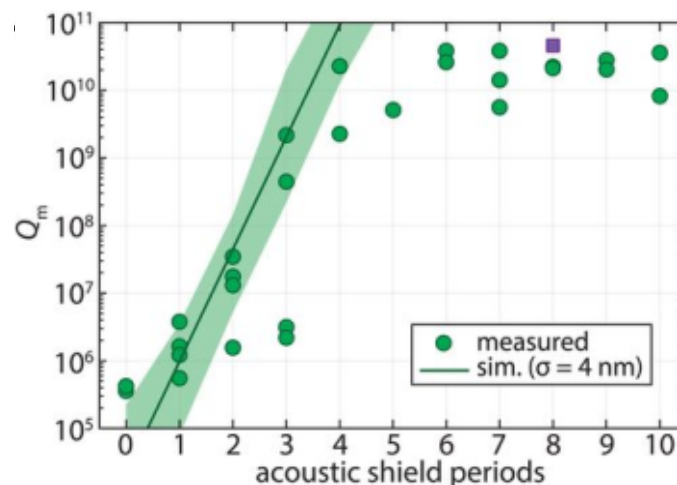


Hybrid systems enhancing quantum computing



Phononic crystal resonators could form a memory for superconducting qubit

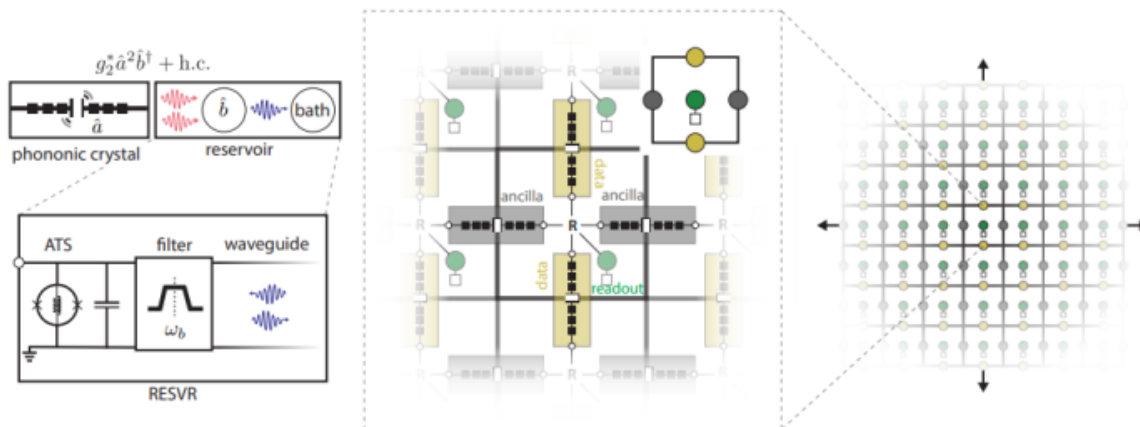
- second-scale long lifetimes compared to 100 μ s lifetimes for transmon qubits



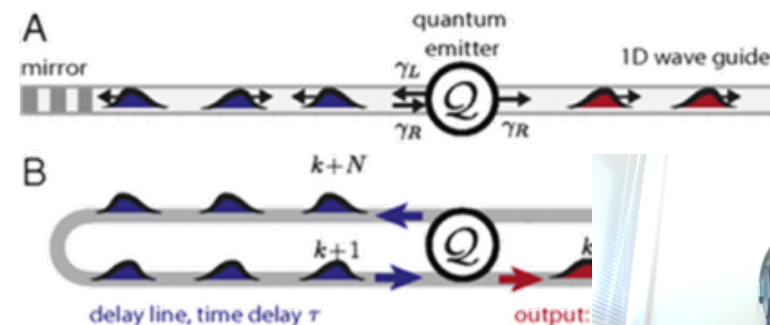
Science 370, 6518, 840 (2020)

A quantum processor build from phononic crystal resonators

Potential universal computing with entangled phonons



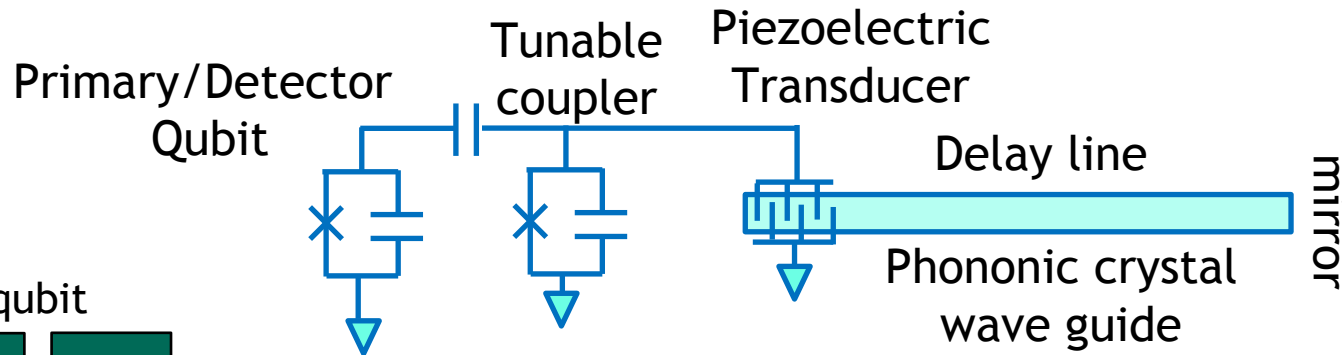
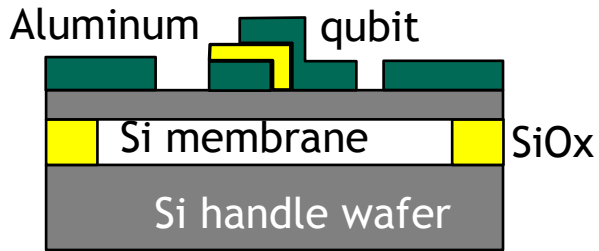
arxiv:2012.04108



PNAS 14 43 (2017)



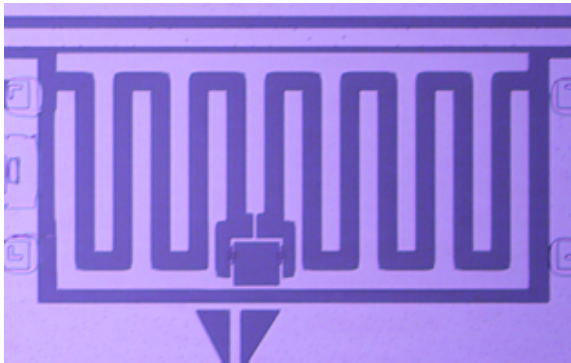
Phononic quantum state generator



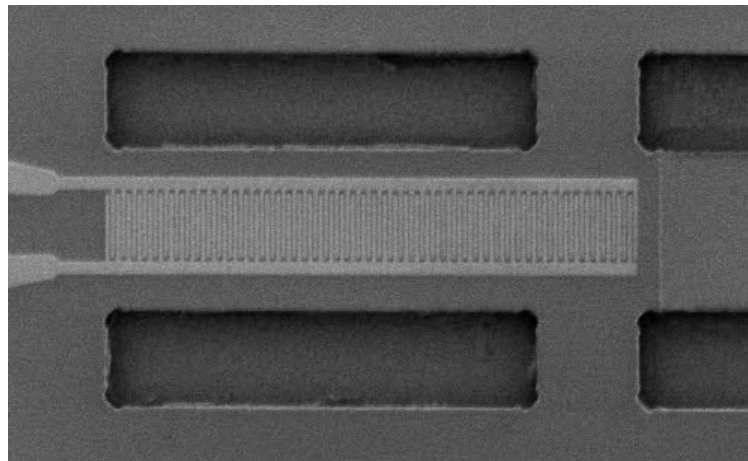
Sandia fabricated components

Piezoelectric Transducer

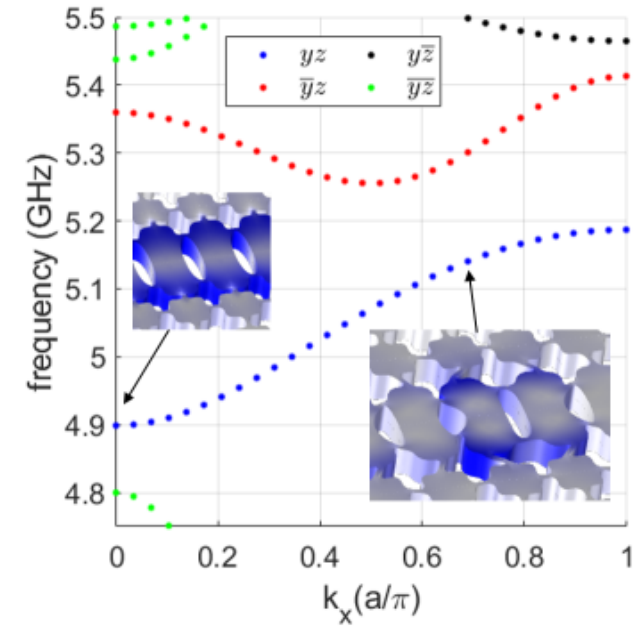
Qubit on solid Si substrate



180 μm

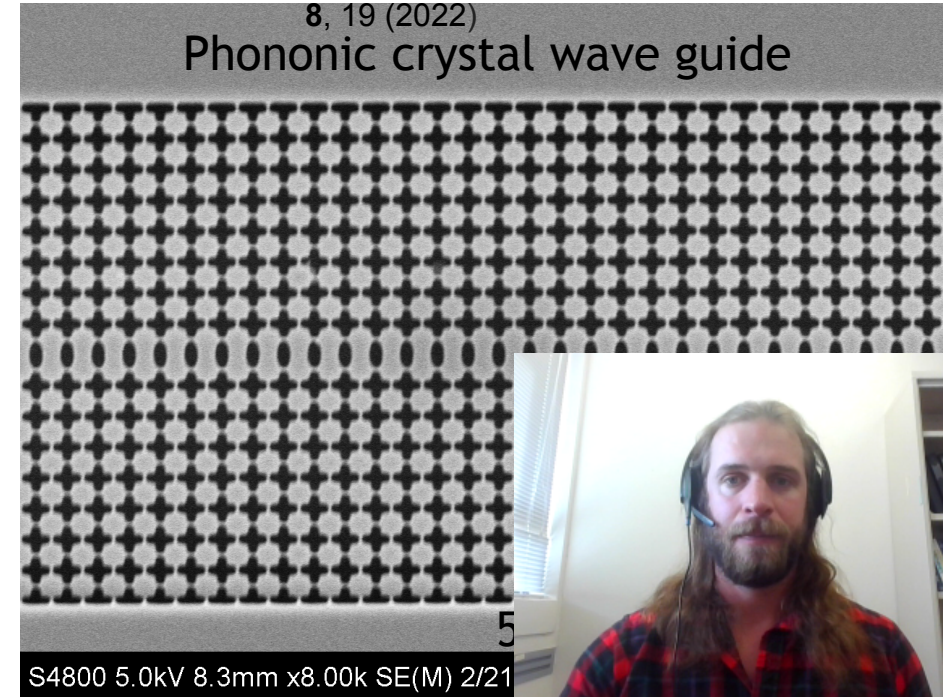


100 μm



npj Quantum Information
8, 19 (2022)

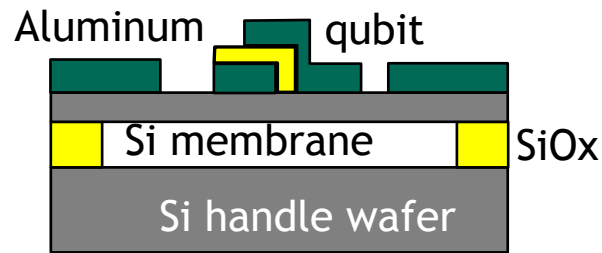
Phononic crystal wave guide



Contributions to microwave loss in devices on silicon membranes are not fully understood

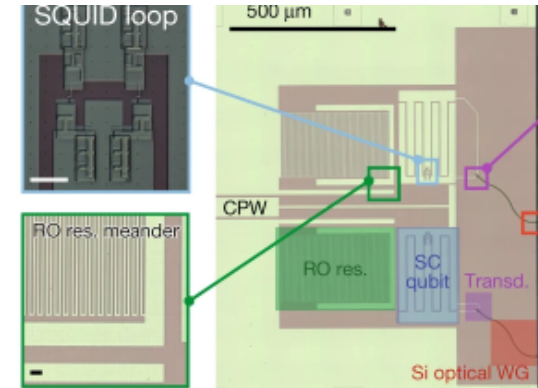


Examples of qubit on Si membrane's have much shorter lifetimes than on solid Si or sapphire substrates.



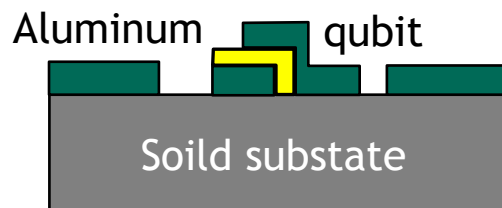
$$T_{1,q} = 522 \pm 9 \text{ ns}$$

$$Q_q = 16,400$$



[Nature](#) **588**, 599–603 (2020)

Extensive body of work looking at contributions to losses in qubits on bulk Si substrates

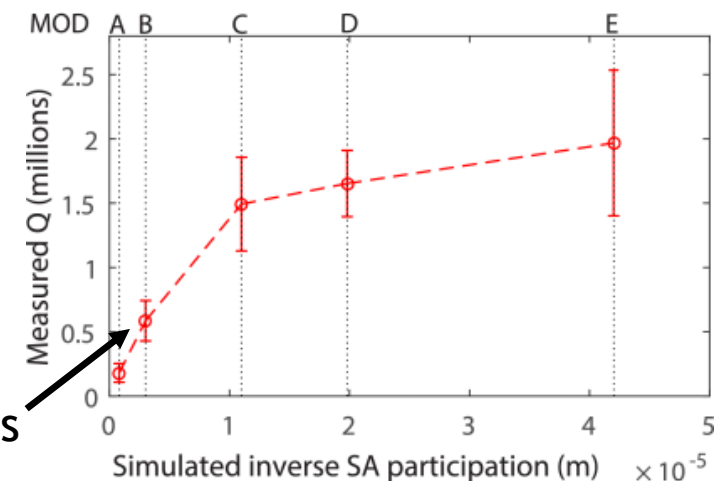


Loss mechanisms

- Dielectric material loss
- Defects and two-level-systems at surface and interfaces

State of the art $T_{1,q} = 20$ to 100's μs

surface loss dominates

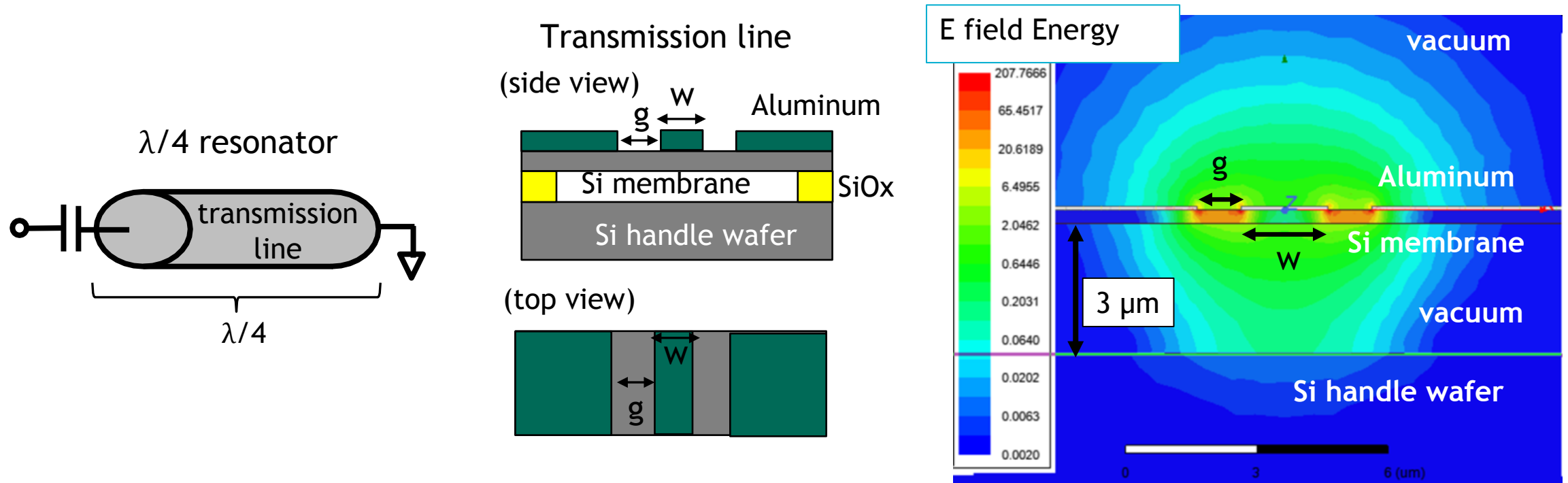


J. M. Gambetta et al., *IEEE Transactions on Applied Superconductivity*, 27, 1, 1-5, Jan. 2017

Differentiating contributions to microwave loss in resonators on Si membranes



To differentiate surface loss from bulk loss, we fabricate resonators with varying designs



ANSYS HFSS

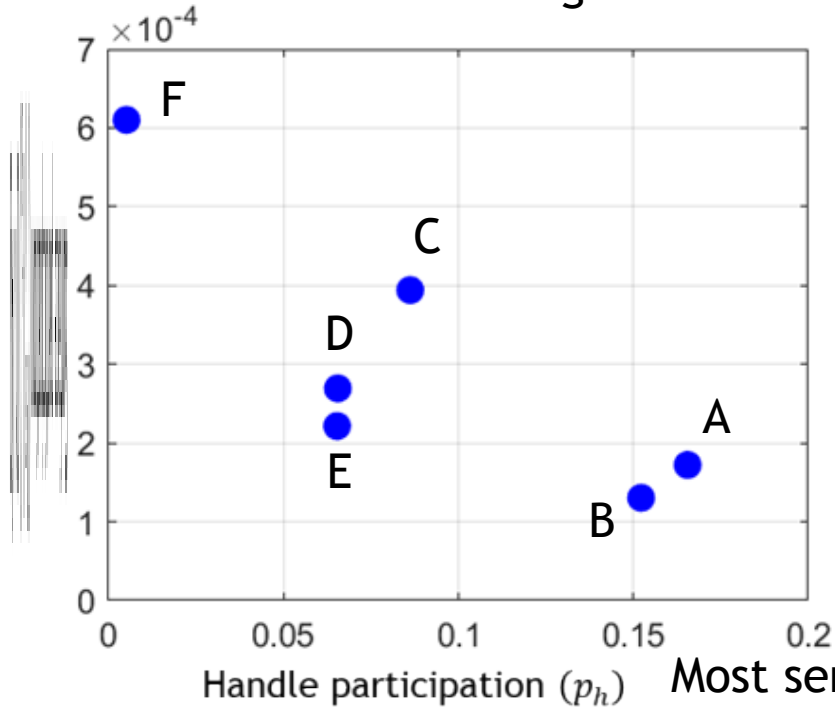
Handle participation $p_h = \frac{\int_{\text{handle}} \mathbf{E} \cdot \mathbf{E} \epsilon_h dV}{U_{\text{tot}}}$ goes up with feature size (g, w)

Surface participation $p_s/t_s = \frac{\int_s \mathbf{E} \cdot \mathbf{E} \epsilon_i dS}{U_{\text{tot}}}$ goes down with feature size (g, w)

Devices to study contributions to microwave loss on Si membranes

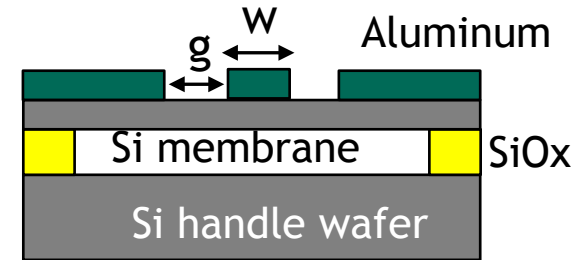
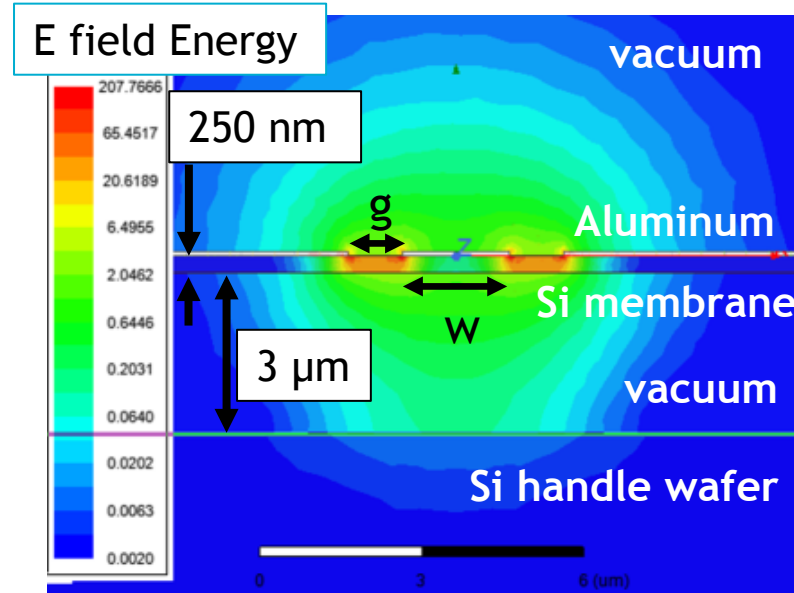


Most sensitive to surface loss Resonator designs



ANSYS HFSS calculation

Most sensitive to handle wafer loss



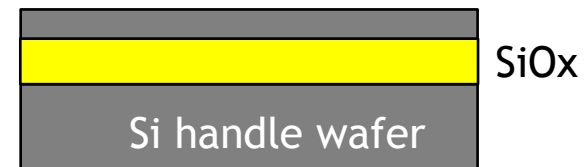
Resonator Design	g (μm)	w (μm)	Surface energy participation (1/Å)	Handle energy participation
A	2	32	1.721 × 10 ⁻⁴	0.1655
B	3	19.5	1.303 × 10 ⁻⁴	0.1522
C	1	24	3.941 × 10 ⁻⁴	0.0862
D	2	9	2.692 × 10 ⁻⁴	0.0655
E	3	6	2.214 × 10 ⁻⁴	0.0653
F	1	2	6.101 × 10 ⁻⁴	0.0051

Fabricate devices on Si membranes

Fabricate on in-stock Si on insulator (SOI) wafers with lossy handle

Si membrane: high resistivity

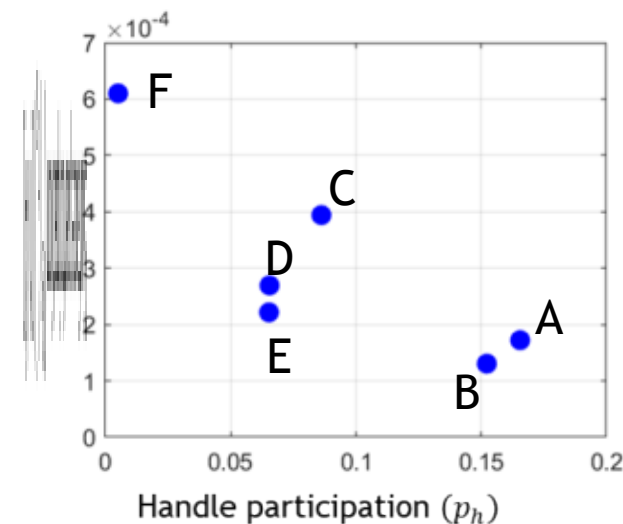
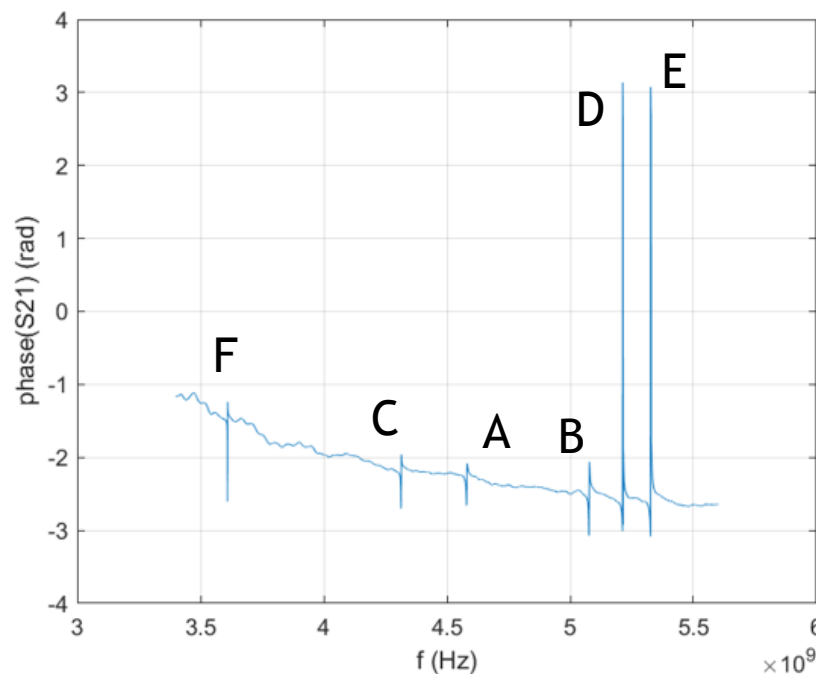
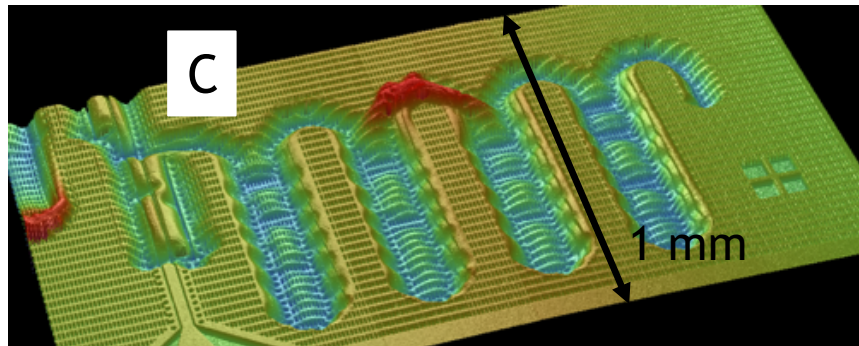
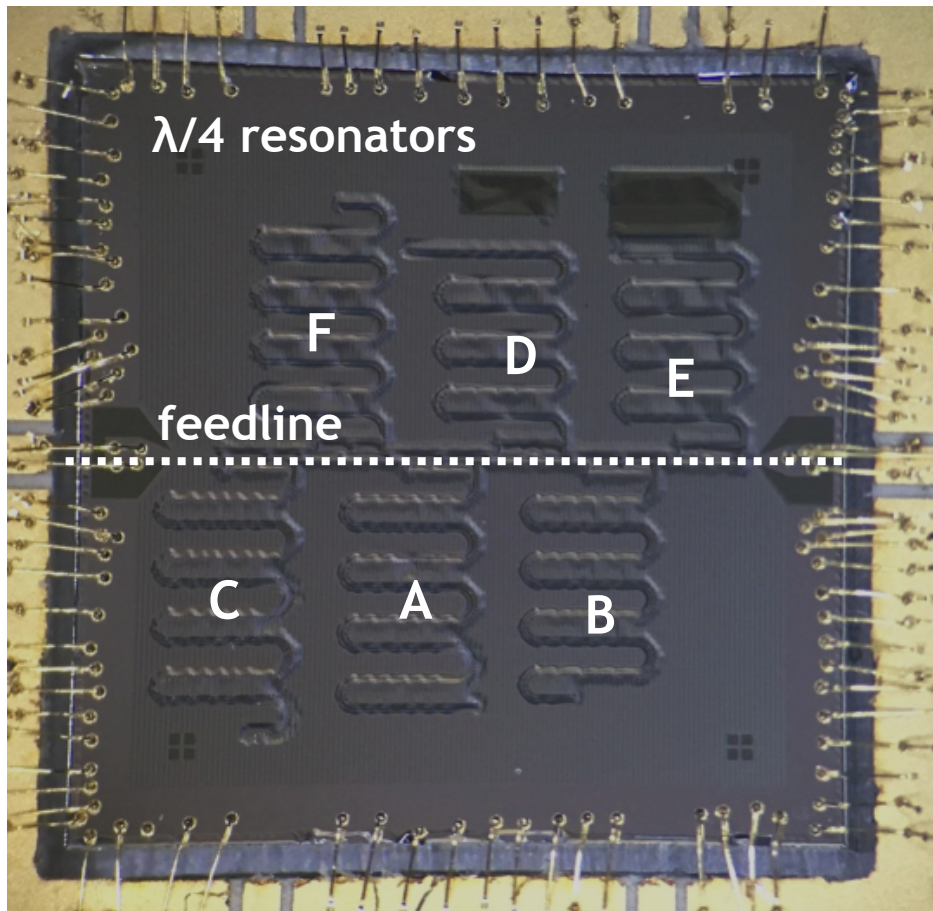
$> 5000 \Omega \cdot \text{cm}$



Si Handle wafer:

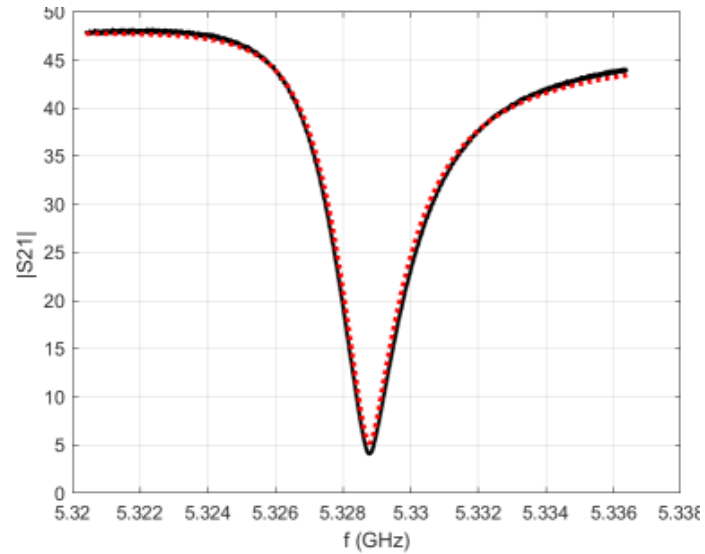
moderate resistivity (lossy)

14 to $22 \Omega \cdot \text{cm}$

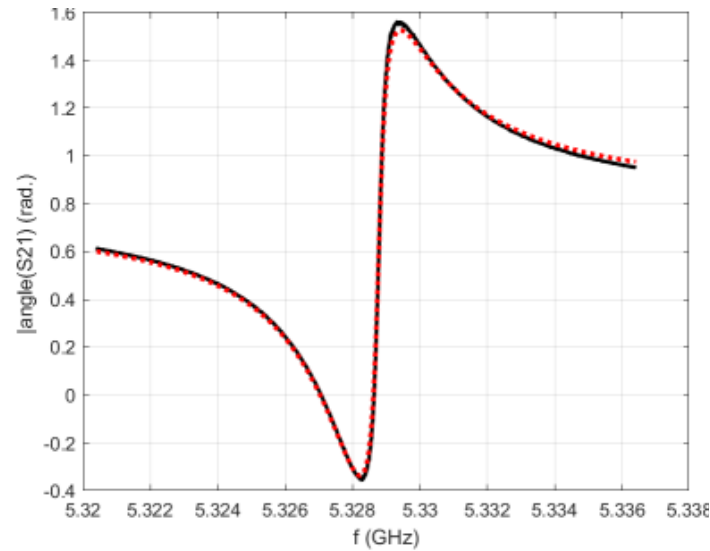


Expect to be most sensitive to handle wafer loss

Extract internal loss with transmission measurements



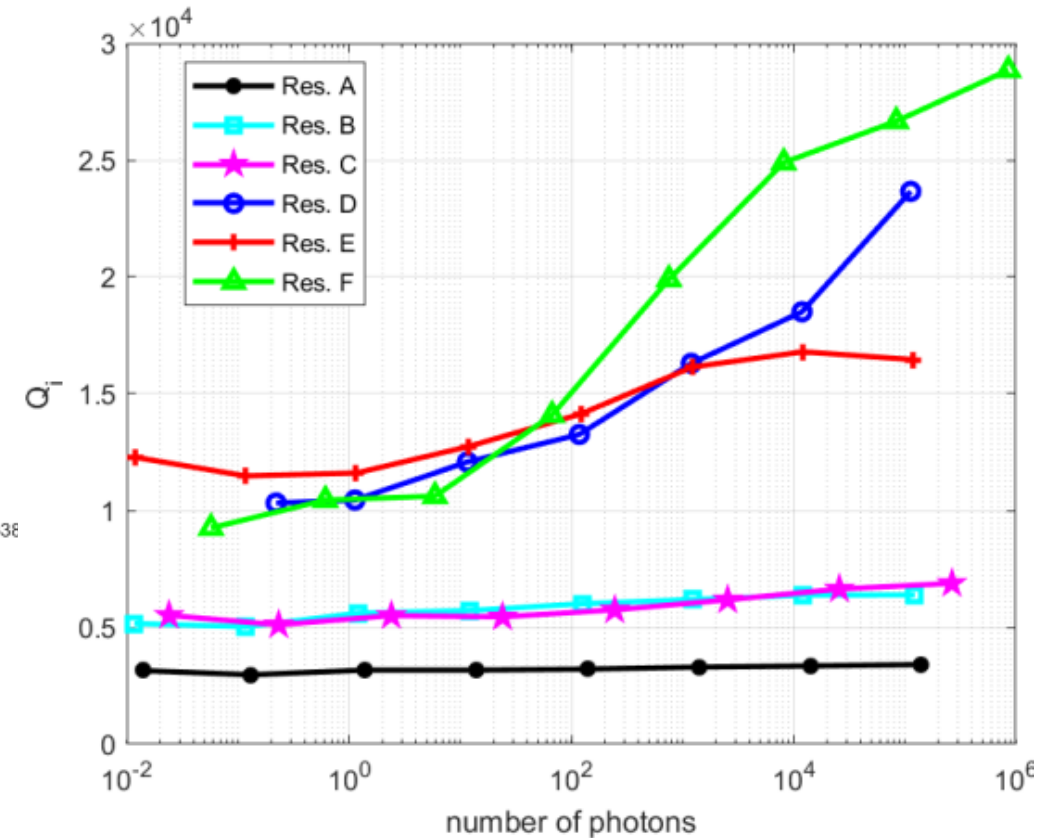
$$\omega_0/2\pi = 5.3294 \text{ GHz}$$



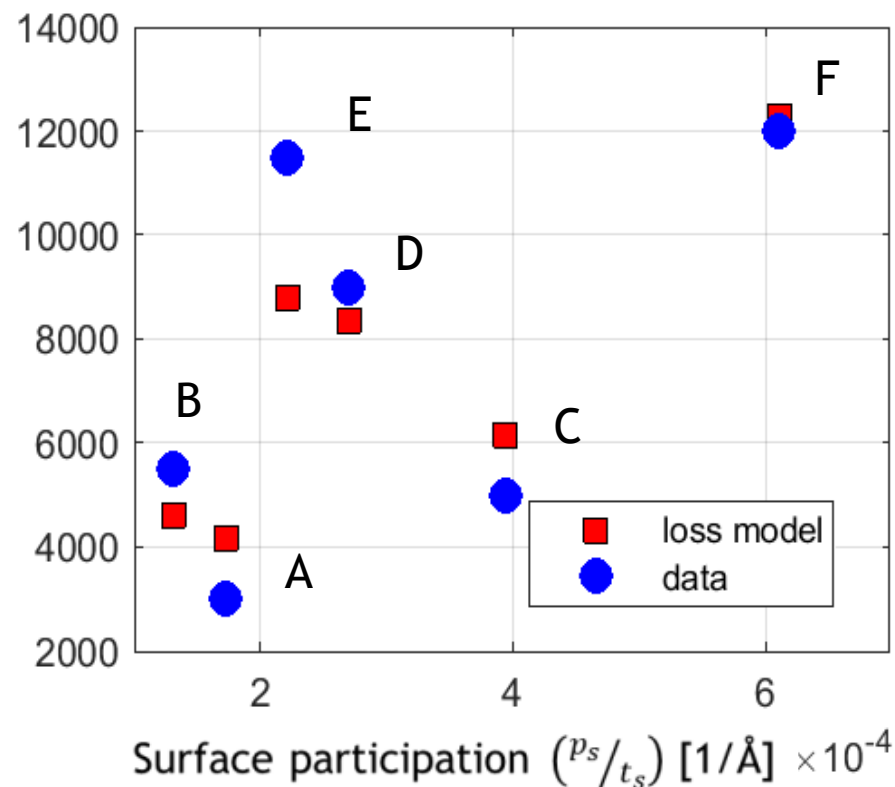
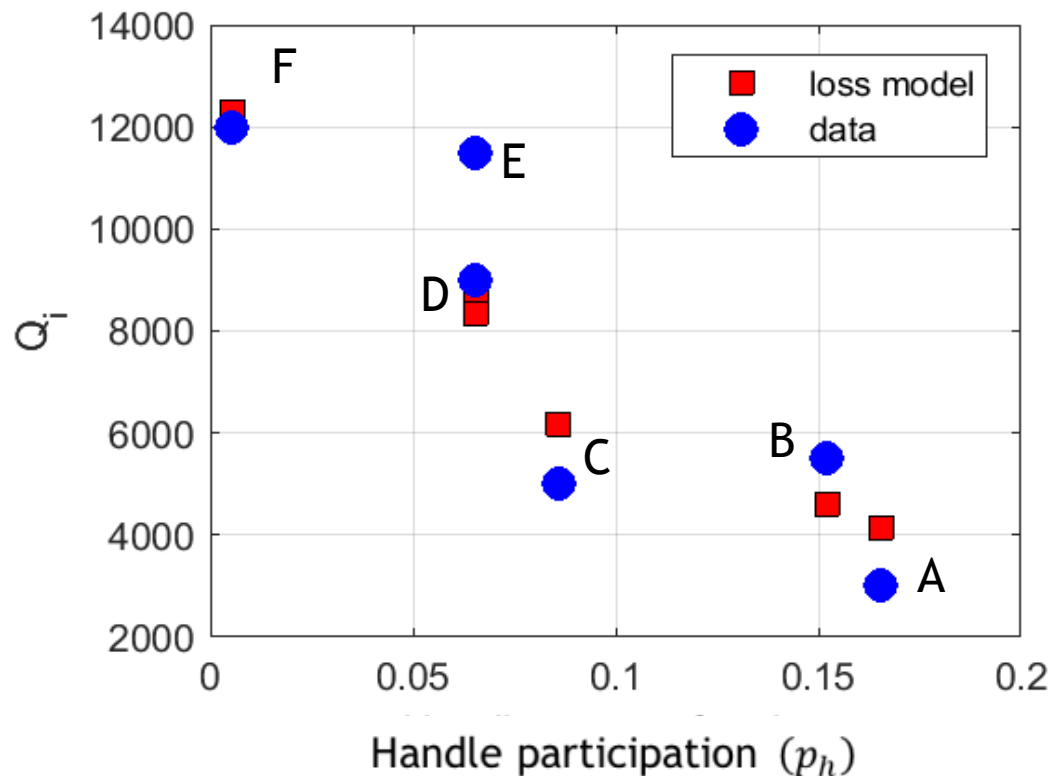
$$Q_i = 13436$$

$$Q_e = 1751$$

$$S_{21} = A_0 e^{-i(\omega\tau + \phi)} \left(1 - \frac{Q_i - 2iQ_e Q_i \frac{\delta\omega}{\omega_0}}{(Q_e + Q_i) + 2iQ_e Q_i \frac{\omega - \omega_0}{\omega_0}} \right)$$



Results and loss model



loss model
$$\frac{1}{Q_i} = \tan(\delta_h) p_h + \eta_s \frac{p_s}{t_s}$$

Bulk loss in handle

loss tangent $\tan \delta_h = 0.0013$

Surface loss

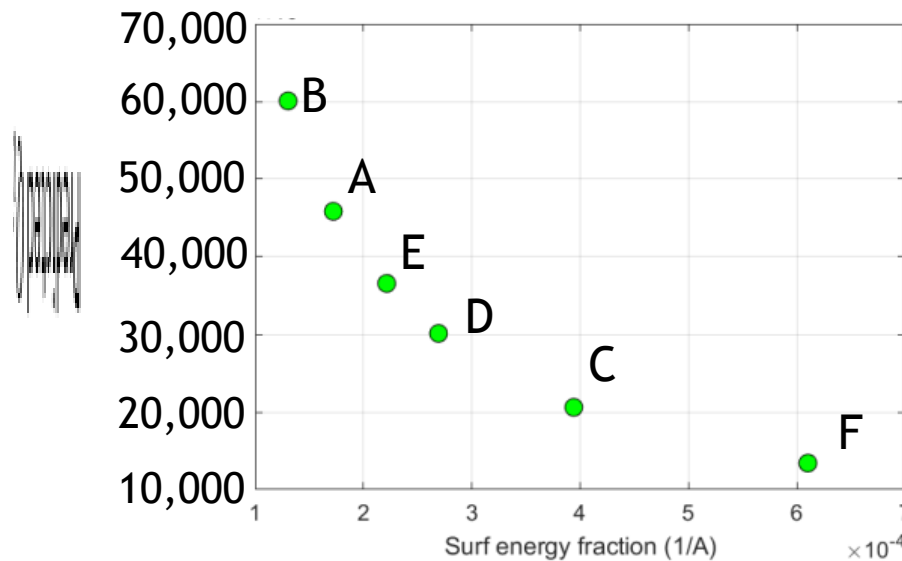
$\eta_s = 0.122 \text{ \AA}$

Handle dominate loss as expected for
14 to 22 $\Omega \cdot \text{cm}$ handle wafer

Conclusions



- Demonstrated a method to determine contribution of loss in superconducting devices on Si membranes
- Applied this method to devices on a lossy Si handle wafer
- Will apply to high resistivity (low loss) handle wafers when they arrive (supply chain issues!)



- Will fabricate qubits on low loss handle wafers and then integrate with phonon crystal waveguides

Questions: contact me <wkindel@sandia.gov>

Interested in being a postdoc: contact me or Matt Eichenfield <meichen@sandia.gov>